UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/681,643	05/15/2001	Takatoshi Tsujimura	JP920000112US1	8744

877 7590 02/13/2004

IBM CORPORATION, T.J. WATSON RESEARCH CENTER
P.O. BOX 218
YORKTOWN HEIGHTS, NY 10598

EXAMINER	
COLEMAN, WILLIAM D	
ART UNIT	**PAPER NUMBER**
2823	

DATE MAILED: 02/13/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	09/681,643	TSUJIMURA ET AL.	
	Examiner	Art Unit	
	W. David Coleman	2823	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 2 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1)☒ Responsive to communication(s) filed on *11 September 2003*.

2a)☒ This action is **FINAL**. 2b)☐ This action is non-final.

3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4)☒ Claim(s) *1-16* is/are pending in the application.

4a) Of the above claim(s) *13-16* is/are withdrawn from consideration.

5)☐ Claim(s) _____ is/are allowed.

6)☒ Claim(s) *1-12* is/are rejected.

7)☐ Claim(s) _____ is/are objected to.

8)☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9)☐ The specification is objected to by the Examiner.

10)☐ The drawing(s) filed on _____ is/are: a)☐ accepted or b)☐ objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11)☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12)☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a)☐ All b)☐ Some * c)☐ None of:

1.☐ Certified copies of the priority documents have been received.

2.☐ Certified copies of the priority documents have been received in Application No. _____.

3.☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) ☐ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date _____.
4) ☒ Interview Summary (PTO-413) Paper No(s)/Mail Date. _____.
5) ☐ Notice of Informal Patent Application (PTO-152)
6) ☐ Other: _____.

DETAILED ACTION

Response to Arguments

Applicant's arguments filed September 11, 2003 have been fully considered but they are not persuasive.

Applicant contends that the prior art rejection of Ohnuma et al, U.S. Patent 6,072,193 in view of Gardner et al., U.S. Patent 6,066,519 fails to teach Applicants' invention because Applicant has a different reasoning for depositing an oxide on the substrate walls. Applicant further contends that the oxide on the inner walls is to prevent P-containing chemical species, such as phosphine (PH3), from sticking to the chamber walls.

In response to applicant's argument that the inner walls coated with an oxide prevents phosphine from sticking to the chamber walls, the fact that applicant has recognized another advantage which would flow naturally from following the suggestion of the prior art cannot be the basis for patentability when the differences would otherwise be obvious. See *Ex parte Obiaya*, 227 USPQ 58, 60 (Bd. Pat. App. & Inter. 1985).

In response to applicant's argument that the references fail to show certain features of applicant's invention, it is noted that the features upon which applicant relies (i.e., the inner walls coated with an oxide prevents phosphine from sticking to the chamber walls) are not recited in the rejected claim(s). Although the claims are interpreted in light of the specification, limitations from the specification are not read into the claims. See *In re Van Geuns*, 988 F.2d 1181, 26 USPQ2d 1057 (Fed. Cir. 1993).

Please note that the amendment filed September 11, 2003 does not further limit nor distinguish Applicants claimed invention because the prior art references teaches forming an oxide film, prior to forming a source/drain region (see bottom gate tft, figures 9A-10D)

This Office Action is a response to address amended claims 11 and 12 which do not conform to the revised amendment practice of 37 CFR 1.121 effective date of July 30, 2003 which require Applicant/Applicant's to include a complete listing of all claims in the Application.

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

> (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

2. Claims 1-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ohnuma et al., U.S. Patent 6,072,193 in view of Gardner et al., U.S. Patent 6,066,519.

3. Pertaining to claims 1 and 2, Ohnuma discloses a semiconductor process substantially as claimed. See **FIGS. 1A-2D**, where Ohnuma teaches a manufacturing method of an active matrix device (column 17, line 62) including a top gate type TFT, which comprises a process of forming the top gate type TFT, wherein the process of forming the top gate type TFT includes the steps of:

arranging a substrate **101** having source **125** and drain electrodes **126** formed therein in

the processing chamber; doping the source and drain electrodes with P (phosphorous), (column 3, lines 51-54); and forming an a-Si layer **103** and a gate insulating film **104** in the processing chamber; and

wherein forming the oxide film on the inner wall of the CVD processing chamber is performed before doping the source and drain electrodes with P. However, Ohnuma fails to disclose forming an oxide film on an inner wall of a CVD processing chamber. Gardner teaches forming an oxide on an inner wall of a CVD processing chamber (column 6, lines 8-14). In view of Gardner, it would have been obvious to one of ordinary skill in the art because when forming a gate dielectric residual oxide forms on the chamber walls (column 6, lines 10-12).

4. Pertaining to claim 2, Ohnuma fails to disclose removing the oxide film form the inner wall after the step of forming the a-Si layer and the gate insulating layer. Gardner teaches the step of removing oxide between runs. In view Gardner, it would have been obvious to one of ordinary skill in the are to remove oxide from the chamber walls after the step of forming the a-Si layer and the gate insulating film because the a silicon gate dielectric layer may be formed in a highly controlled manner (column 6, lines 21-23).

5. Pertaining to claim 3, Ohnuma teaches a manufacturing method of an active matrix device according to claim 1,

wherein the oxide film contains SiOx.

6. Pertaining to claim 4, Ohnuma teaches a manufacturing method of an active matrix device according to claim 1, wherein the active matrix device is a liquid crystal display (column 17, line 62).

7. Pertaining to claim 5, Ohnuma teaches a manufacturing method of an active matrix device according to claim 1, wherein the active matrix device is an electroluminescence display (column 17, line 62).

8. Pertaining to claim 6, Ohnuma teaches a manufacturing method of an active matrix device according to claim 2, wherein the oxide film contains SiOx.

9. Pertaining to claim 7, Ohnuma teaches a manufacturing method of an active matrix device according to claim 2, wherein the active matrix device is a liquid crystal display.

10. Pertaining to claim 8, Ohnuma teaches a manufacturing method of an active matrix device according to claim 3, wherein the active matrix device is a liquid crystal display.

11. Pertaining to claim 9, Ohnuma teaches a manufacturing method of an active matrix device according to claim 2, wherein the active matrix device is an electroluminescence display.

12. Pertaining to claim 10, Ohnuma teaches a manufacturing method of an active matrix device according to claim 3, wherein the active matrix device is an electroluminescence display.

13. Pertaining to claim 11, Ohnuma fails to teach a manufacturing method of an active matrix device according to claim 1, further comprising heating the inner wall of the CVD processing chamber. Gardner teaches further comprising heating the inner wall of the CVD processing chamber (column 3, lines 22-60). In view of Gardner, it would have been obvious to one of ordinary skill in the art to incorporate the manufacturing method of Gardner into the Ohnuma semiconductor process because it would benefit from the use of an extremely thin oxide layer (column 3, lines 13-14).

14. Pertaining to claim 12, Ohnuma teaches a manufacturing method of an active matrix device according to claim 1, wherein the oxide film is selected from the group consisting of SiO_x, Al_2O_3, TiO_2, $Al_2(Si_2O_5)(OH)_4$, $MgAl_2O_4$, TaO_x, and ZrO_x.

Conclusion

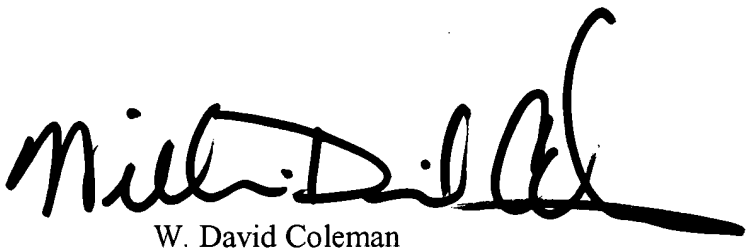
15. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

16. A shortened statutory period for reply to this final action is set to expire TWO MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

17. Any inquiry concerning this communication or earlier communications from the examiner should be directed to W. David Coleman whose telephone number is 571-272-1856. The examiner can normally be reached on 9:00 AM-5:00 PM.

18. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 703-306-2794. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

19. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



W. David Coleman
Primary Examiner
Art Unit 2823

WDC